

Enhanced photovoltaic output of bifacial perovskite solar cells via tailoring photoelectric balance in rear window layers with 1T-WS₂ nanosheets engineering

Lin Fan,^{ab} Wanhong Lü,^a Wanting Hu,^a Donglai Han,^c Shuo Yang,^d Dandan Wang,^e Zhihong Mai,^e Fengyou Wang,^{ab} Huilian Liu,^{ab} Jinghai Yang,^{**ab} and Lili Yang^{*ab}

^a Key Laboratory of Functional Materials Physics and Chemistry of the Ministry of Education, Jilin Normal University, Changchun 130103, China

^b National Demonstration Center for Experimental Physics Education, Jilin Normal University, Siping 136000, China

^c School of Materials Science and Engineering, Changchun University of Science and Technology, Changchun 130022, China

^d College of Science, Changchun University, Changchun 130022, China

^e Hubei JiuFengShan Laboratory, Future Science and Technology City, Wuhan, Hubei, 420000, China

E-mail addresses: llyang1980@126.com (Lili Yang), jhyang1@jlnu.edu.cn (Jinghai Yang).

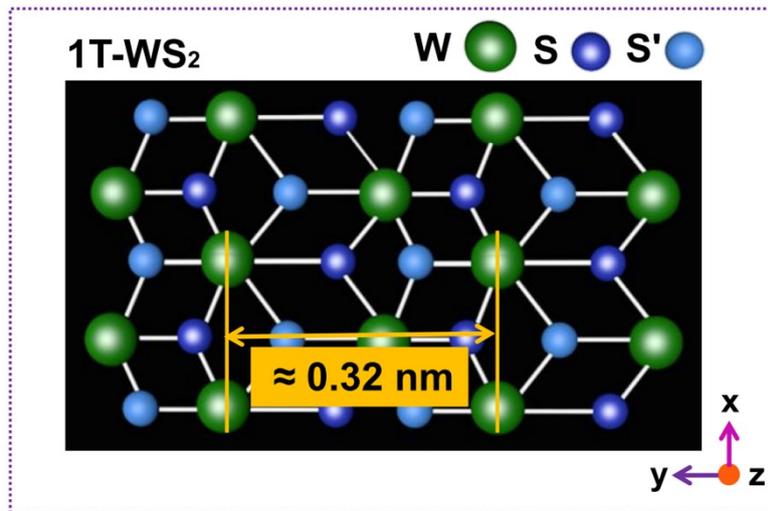


Fig. S1 Top-view molecule structures of 1T-WS₂. W atoms are in green and S atoms are in purple and blue for top and bottom layers, respectively.

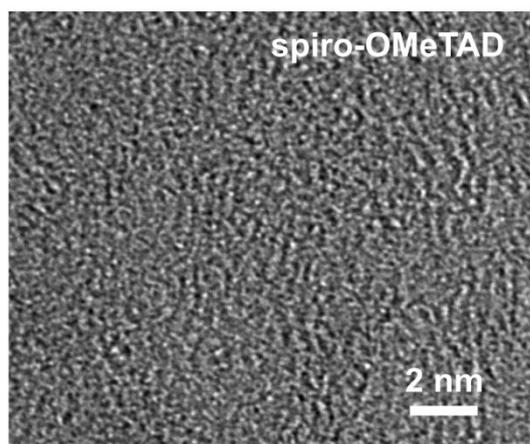


Fig. S2 HRTEM image of spiro-OMeTAD film.

Fig. S3 (a) Raman spectra of SP and SP + W films. (b) Surface SEM image and elemental mappings (W and S) of SP + W film.

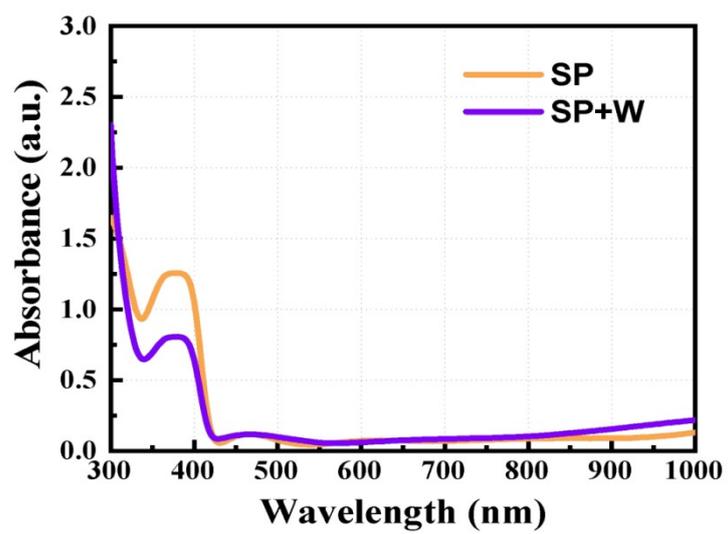


Fig. S4 UV-vis absorption spectra of SP and SP + W films.

Fig. S5 (a) TRPL plots and fitting curves of Glass/PVK/SP and Glass/PVK/SP + W substrates. (b) Nyquist plots of solar cells based on SP and SP + W HTLs, obtained with a bias of 0.8 V in dark. Inset: equivalent circuit used to fit the data.

Fig. S6 (a) OCVD curves and (b) dark-current measurements of the corresponding devices.

Fig. S7 Optimization of the optical and electrical properties of different SP + W films deposited on ITO-glass substrates: (a) transmittance, (b) UV-vis absorption, and (c) conductivity.

Fig. S8 (a) J - V curves of the best-performing SP-based b-PSC illuminated on different sides. (b) Corresponding EQE spectra and integrated J_{SC} .

Fig. S9 Steady-state current densities measured at the voltage of the maximum power point for (a) SP and (b) SP + W b-PSCs.

Table S1 Hall measurement results of SP and SP + W films

Samples	Conductivity	Resistivity	Hall Mobility	Thickness
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	(S/cm)	($\Omega \cdot \text{cm}$)	($\text{cm}^2/\text{V} \cdot \text{s}$)	(nm)
SP	5.00×10^{-7}	2.00×10^6	3.57×10^{-3}	~ 230 nm
SP + W	6.57×10^{-5}	1.50×10^4	6.04×10^{-3}	~ 150 nm

Table S2 Fitting parameters from EIS

Samples	R_s (Ω)	R_{tr} (Ω)	R_{rec} (Ω)	C_{tr} (F)	C_{rec} (F)
SP	34.21	24.66	383.3	7.3×10^{-9}	5.6×10^{-9}
SP + W	27.86	18.81	468.3	7.1×10^{-9}	6.4×10^{-9}

Experimental section

Materials and reagents:

Etched indium-doped tin oxide (ITO, $2 \times 2 \text{ cm}^2$) conducting glasses were purchased from Yingkou Optimum Trade Co., Ltd., whereas tin oxide colloidal dispersion (SnO_2 15% in H_2O colloidal dispersion), dimethyl sulfoxide (DMSO, $\geq 99.8\%$), N,N-dimethylformamide (DMF, $\geq 99.8\%$), and methylammonium iodide ($\text{CH}_3\text{NH}_3\text{I}$, MAI, $\geq 99.8\%$) were purchased from Alfa Aesar. Lead (II) iodide (PbI_2 , $\geq 99.999\%$) and chlorobenzene (CB, $\geq 99.5\%$) were obtained from Sigma-Aldrich and Aladdin Reagent, respectively. Tungsten disulfide nanosheet powder (WS_2 , average lateral size: $\sim 100 \text{ nm}$) was purchased from Nanjing XFNANO Materials Co., Ltd. The 2,2',7,7'-tetrakis [N,N-di(4-meth-oxyphenyl)amino]-9,9'-spirobifluorene (spiro-OMeTAD, $\geq 99.0\%$), sulfonyl imide (Li-TFSI, $\geq 99\%$), acetonitrile ($\geq 99.9\%$), and 4-tertbutylpyridine (TBP, $\geq 99\%$) were supplied by Yingkou Optimum Trade Co., Ltd. The purity of the silver (Ag) used for thermally evaporated electrode was 99.99%. All chemicals and reagents were directly used without further purification.

Materials and devices characterization:

Transmission electron microscopy (TEM) images were taken using a JEOL-2010 TEM operating at a 200 kV accelerating voltage. The surface and cross-sectional morphologies of samples were measured using a field-emission scanning electron microscopy (SEM, JEOL, JSM-7800F). The material states of samples were characterized by means of Raman spectroscopy (Nanofinder 30, Tokyo Instruments Inc.), using laser excitation with a 514 nm wavelength. The optical properties, including transmission and absorption, were recorded on an UV-vis spectrophotometer (SHTMADZU, UV-3600plus). The relevant electrical parameters of different films were analyzed by a four-point probe system with a current source-

meter (RS8, BEGA Technologies). X-ray photoelectron spectroscopy (XPS) and ultraviolet photoelectron spectroscopy (UPS) were performed using an XPS/UPS system (ThermoFisher, Excalab 250 xi). The chemical composition and state analysis of samples were measured by XPS, and the energy band structure was evaluated by UPS with the He I (21.22 eV) emission line employed for excitation. The surface potentials of films were measured with Kelvin probe force microscope (KPFM, Park Systems NX20, Korea). The time-resolved photoluminescence (TRPL) spectrum was measured by a Fluorolog-3-TCSPC spectrometer (Edinburgh Instruments, FLS1000, UK). The electrochemical impedance spectroscopy (EIS) of solar cells was performed using an electrochemical workstation (CHI660C) at a voltage bias of 0.8 V in dark. The photocurrent density-voltage ($J-V$) curves of solar cells with different incident light directions were acquired using a solar simulator (Newport Oriel Solar 3A Class AAA) equipped with a 150-W xenon lamp under AM 1.5G (100 mW/cm²) simulated sunlight. Light intensity was calibrated using a standard KG3-filtered silicon reference cell certified by the National Renewable Energy Laboratory. All devices were reverse scanned (from 1.2 V to - 0.2 V) at a scan rate of 130 mV/s, and the active area was delimited using the metal mask. The spectral response of devices was taken by an external quantum efficiency (EQE) measurement system (Newport, IQE 200TM), equipped with a monochromator, a lock-in amplifier, a Xe lamp, and a current-voltage amplifier.